

CLAIMS

This listing of claims will replace all prior versions, and listings of claims in the application.

1. (Previously presented) A method of washing a photomask comprising:
removing organic matter and metal impurities present on the surface of a photomask;
removing foreign matter adhering to said surface of said photomask with H₂ gas dissolved water; and
drying said photomask,
wherein said photomask is a phase-shift mask including halftone mask, said H₂ gas dissolved water contains ammonia and the concentration of said ammonia is not more than 1%.
2. (Original) The method of washing a photomask in accordance with claim 1, wherein said H₂ gas dissolved water is alkalized.
3. (Original) The method of washing a photomask in accordance with claim 2, wherein said H₂ gas dissolved water is alkalized with ammonia.
4. (Original) The method of washing a photomask in accordance with claim 2, wherein said H₂ gas dissolved water is alkalized with KOH.
5. (Currently amended) The method of washing a photomask in accordance with claim 1, also employing ultrasonics waves in said second step of removing foreign matter.

6. (Previously presented) The method of washing a photomask in accordance with claim 5, wherein said step of removing organic matter and metal impurities employs ultrasonics waves.

7. (Currently amended) The method of washing a photomask in accordance with claim 5, wherein said foreign matter ~~if~~ is particulate foreign matter.

8-14. (Cancelled)

15. (Previously presented) The method of washing a photomask in accordance with claim 1, wherein said phase-shift photomask is formed with an MoSiON film.